

Abstract of the Disclosure

Method and apparatus for improving the high current operation of bipolar transistors while minimizing adverse affects on high frequency response are disclosed. A local implant to increase the doping of the collector at the collector to base interface is achieved by the use of an angled ion implant of collector impurities through the emitter opening. The resulting area of increased collector doping is larger than the emitter opening, which minimizes carrier injection from the emitter to the collector, but is smaller than the area of the base.

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